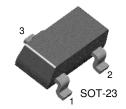


### KST3904

### **General Purpose Transistor**



### 1. Base 2. Emitter 3. Collector

### **NPN Epitaxial Silicon Transistor**

### **Absolute Maximum Ratings** $T_a$ =25°C unless otherwise noted

Symbol	Parameter	Value	Units
V <sub>CBO</sub>	Collector-Base Voltage	60	V
V <sub>CEO</sub>	Collector-Emitter Voltage	40	V
V <sub>EBO</sub>	Emitter-Base Voltage	6	V
l <sub>C</sub>	Collector Current	200	mA
P <sub>C</sub>	Collector Power Dissipation	350	mW
T <sub>STG</sub>	Storage Temperature	150	°C

### **Electrical Characteristics** $T_a$ =25°C unless otherwise noted

Symbol	Parameter	Test Condition	Min.	Max.	Units
BV <sub>CBO</sub>	Collector-Base Breakdown Voltage	I <sub>C</sub> =10μA, I <sub>E</sub> =0	60		V
BV <sub>CEO</sub>	* Collector-Emitter Breakdown Voltage	I <sub>C</sub> =1mA, I <sub>B</sub> =0	40		V
BV <sub>EBO</sub>	Emitter-Base Breakdown Voltage	I <sub>E</sub> =10μA, I <sub>C</sub> =0	6		V
I <sub>CEX</sub>	Collector Cut-off Current	V <sub>CE</sub> =30V, V <sub>EB</sub> =3V		50	nA
h <sub>FE</sub>	* DC Current Gain	$\begin{array}{c} V_{CE} = 1 \text{V, } I_{C} = 0.1 \text{mA} \\ V_{CE} = 1 \text{V, } I_{C} = 1 \text{mA} \\ V_{CE} = 1 \text{V, } I_{C} = 10 \text{mA} \\ V_{CE} = 1 \text{V, } I_{C} = 50 \text{mA} \\ V_{CE} = 1 \text{V, } I_{C} = 100 \text{mA} \end{array}$	40 70 100 60 30	300	
V <sub>CE</sub> (sat)	* Collector-Emitter Saturation Voltage	I <sub>C</sub> =10mA, I <sub>B</sub> =1mA I <sub>C</sub> =50mA, I <sub>B</sub> =5mA		0.2 0.3	V V
V <sub>BE</sub> (sat)	* Base-Emitter Saturation Voltage	$I_C$ =10mA, $I_B$ =1mA $I_C$ =50mA, $I_B$ =5mA	0.65	0.85 0.95	V V
C <sub>ob</sub>	Output Capacitance	V <sub>CB</sub> =5V, I <sub>E</sub> =0, f=1MHz		4	pF
f <sub>T</sub>	Current Gain-Bandwidth Product	V <sub>CE</sub> =20V, I <sub>C</sub> =10mA, f=100MHz 300			MHz
NF	Noise Figure	$I_{C}$ =100μA, $V_{CE}$ =5V, $R_{S}$ =1KΩ 5 f=10Hz to 15.7KHz		5	dB
t <sub>ON</sub>	Turn On Time	$V_{CC}$ =3V, $V_{BE}$ =0.5V 70 $I_{C}$ =10mA, $I_{B1}$ =1mA		70	ns
t <sub>OFF</sub>	Turn Off Time	V <sub>CC</sub> =3V, I <sub>C</sub> =10mA, I <sub>B1</sub> =I <sub>B2</sub> =1mA		250	ns

<sup>\*</sup> Pulse Test: Pulse Width≤300μs, Duty Cycle≤2%



# **Typical Characteristics**

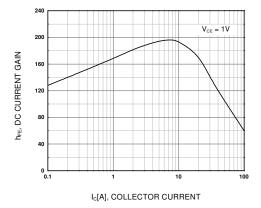


Figure 1. DC current Gain

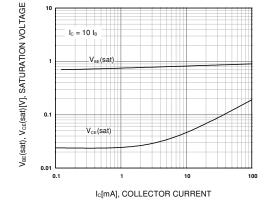


Figure 2. Base-Emitter Saturation Voltage Collector-Emitter Saturation Voltage

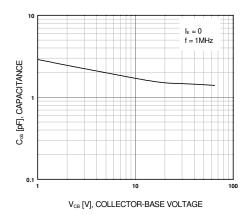


Figure 3. Output Capacitance

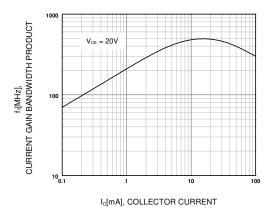
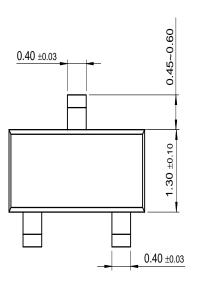
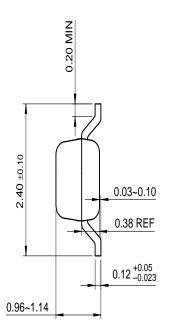


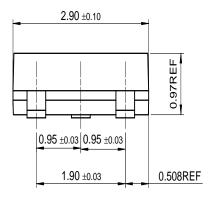
Figure 4. Current Gain Bandwidth Product

# **Package Dimensions**

# SOT-23







Dimensions in Millimeters

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CoolFET™	FASTr™	MicroFET™	PowerTrench <sup>®</sup>	SuperSOT™-6
CROSSVOLT™	FRFET™	MicroPak™	QFET™	SuperSOT™-8
DOME™	GlobalOptoisolator™	MICROWIRE™	QS <sup>TM</sup>	SyncFET™
EcoSPARK™	GTO™	MSX™	QT Optoelectronics™	TinyLogic™
E <sup>2</sup> CMOS™	HiSeC™	MSXPro™	Quiet Series™	TruTranslation™
EnSigna™	$I^2C^{TM}$	OCXTM	RapidConfigure™	UHC™
Across the board.	. Around the world.™	OCXPro™	RapidConnect™	UltraFET®
The Power Franchise™		OPTOLOGIC <sup>®</sup>	SILENT SWITCHER®	VCX™
Programmable Active Droop™		OPTOPLANAR™	SMART START™	

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Rev. I1

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